

# Local injection of pure spin current generates electric current vortices

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We show that local injection of pure spin current into an electrically disconnected ferromagnetic–normal-metal sandwich induces electric currents, that run along closed loops inside the device, and are powered by the source of the spin injection. Such electric currents may significantly modify voltage distribution in spin-injection devices and induce long-range tails of spin accumulation.

Injection of pure spin current and its subsequent manipulation in spintronic devices [1] has been viewed as an ultimate realization of “spin electronics”, with electron spin carrying all information, and electron charge playing no role. In classic experiments of Johnson and Silsbee [2], pure spin current was injected into an electrically disconnected device. Since there was no electric current  $\mathbf{j}$  entering or leaving the device, it was tacitly assumed that  $\mathbf{j}$  should also be zero everywhere inside it. Johnson and Silsbee found that spin current injection nevertheless generates a voltage  $V$  between the ferromagnetic (F) and normal (N) elements (Fig. 1). In a diffusive transport regime, where electron momentum relaxes much faster than its spin, such a voltage can be described in terms of the “Valet-Fert model” [3–5], outlined below. Johnson and Silsbee [2] predicted the  $V$  to be proportional to the spin accumulation at the F/N boundary, and independent of the measuring probe position – as long as the electric current was absent, and the F-probe was placed at a point where spin accumulation has relaxed to zero (i.e., further than several spin relaxation lengths  $\lambda_s$  away from the F/N boundary).

This statement is true and transparent in the case of a narrow F/N contact (Fig. 1a). However, if the contact is wide enough for the spin accumulation at the F/N interface to become substantially non-uniform (Fig. 1b), then it is not clear which accumulation value should be used in the Johnson-Silsbee formula. This practical issue was studied [6] numerically on a network of spin-dependent resistors that mimic the Valet-Fert equations. It was

found that  $V$  does depend on the probe position, even if the thickness  $t_F$  of the F layer exceeds  $\lambda_s$  (Fig. 1).

On the one hand, emergence of a non-uniform voltage in a system with non-uniform spin accumulation appears to be natural. On the other hand, a potential gradient in the F region with vanishing non-equilibrium spin accumulation can only mean the presence of electric current. How does this correspond to the absence of  $\mathbf{j}$  in the Johnson-Silsbee picture? The Ref. 6 cannot answer this question: there, electric current was actually entering and leaving the nominally electrically disconnected device. The condition of pure spin current injection was not maintained, and the dependence of voltage on the probe position could be ascribed to this trivial effect.

Here we describe a different phenomenon: even if electric currents do not enter the device, they are still induced inside it. These currents circulate along closed loops that cross the F/N interface, and are maintained by the external source that produces the pure-spin injection. We demonstrate the existence of electric current loops and study their influence on the voltage and spin accumulation distributions. Current loops are akin to Eddy currents generated by oscillating magnetic fields, except that the present phenomenon occurs in a non-equilibrium steady state. We show that such electric vortices are not limited to spin transport, but shall be expected whenever electric current is coupled to another diffusive current by linear relationships with Onsager cross-coefficients.

We will consider only setups with collinear local magnetization. In the Valet-Fert model, carrier distributions for spin  $\sigma = \uparrow, \downarrow$  with respect to the  $\hat{z}$  axis are characterized by different electrochemical potentials  $\mu_\sigma$ . The currents  $\mathbf{j}_\sigma$  [7] carried by the two spin populations are  $\mathbf{j}_\sigma = -D_\sigma \nabla \mu_\sigma$ : in a ferromagnet, the two diffusion coefficients  $D_{\uparrow, \downarrow}$  are different. Conservation of electric current and spontaneous relaxation of spin lead to equations

$$\text{div} \mathbf{j} = 0, \quad \text{div} \mathbf{j}^s = -\frac{\mu_\uparrow - \mu_\downarrow}{\tau_s}, \quad (1)$$

where  $\mathbf{j} = \mathbf{j}_\uparrow + \mathbf{j}_\downarrow$  and  $\mathbf{j}^s = \mathbf{j}_\uparrow - \mathbf{j}_\downarrow$  are electric and spin currents, and  $\tau_s$  is the spin relaxation time. The average potential  $\mu = (\mu_\uparrow + \mu_\downarrow)/2$  is the quantity measured by an ideal voltmeter, while the spin potential  $\mu^s = \mu_\uparrow - \mu_\downarrow$  characterizes the non-equilibrium spin

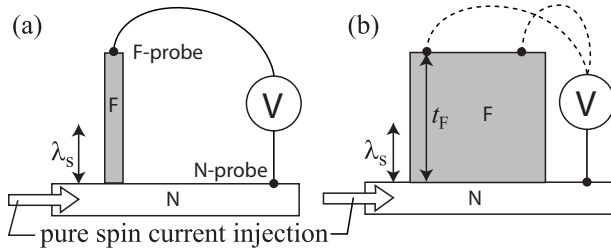


FIG. 1: Electrically disconnected device with pure spin current injected into N-layer from the side; (a) narrow F-electrode (b) wide F-electrode with two different F-probe positions leading to different results for  $V$ .

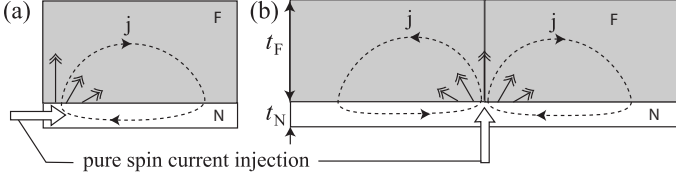


FIG. 2: (a) Device with an extended F-layer. Pure spin current is injected into the N-layer from the side. Double arrows represent the effective EMF generated near the F/N boundary. Dashed line is the generated electric current loop; (b) “Spin fountain”, i.e. symmetric extension of device (a), with pure spin current locally injected into the N-layer from below. For  $t_N \ll \lambda_n$  the currents and potentials in (a) will be approaching those in the right half of (b).

accumulation. The currents  $\mathbf{j}$  and  $\mathbf{j}^s$  can be written as

$$\mathbf{j} = -D(\nabla\mu + \frac{p}{2}\nabla\mu^s) \quad (2)$$

$$\mathbf{j}^s = -\frac{D}{2}(\nabla\mu^s + 2p\nabla\mu) \quad (3)$$

with  $D = D_\uparrow + D_\downarrow$ , and the polarization  $p = (D_\uparrow - D_\downarrow)/D$ . We will consider the  $D$ ,  $p$  and  $\tau_s$  to be piecewise constant, experiencing jumps at interfaces between different materials. The interfaces will be assumed transparent (continuity of  $\mu$  and  $\mu^s$ ) and spin-inactive (continuity of the  $j_\perp^s$  component, normal to the boundary). Together with continuity of  $j_\perp$ , these are the boundary conditions at the interfaces.

Within each uniform region, Eqs. (1-3) yield

$$\Delta\mu = -\frac{p}{2}\Delta\mu^s, \quad \lambda_s^2\Delta\mu^s = \mu^s, \quad (4)$$

with the spin relaxation length  $\lambda_s = \sqrt{\tau_s D(1-p^2)}/2$ .

First, we show that non-uniform spin accumulation near the F/N boundary inevitably produces electric current, even if the latter is not injected from outside. The Eq. (2) implies  $\mathbf{j}/D = \nabla\mu + (p/2)\nabla\mu^s$ , and thus

$$\text{curl}\left(\frac{\mathbf{j}}{D}\right) = \frac{1}{2}\nabla p \times \nabla\mu^s. \quad (5)$$

Now,  $p$  evolves from  $p = 0$  in the normal metal to  $p \neq 0$  in the ferromagnet, thus  $\nabla p \neq 0$ . If  $\nabla\mu^s$  has a component perpendicular to  $\nabla p$ , i.e. if spin accumulation varies along the interface between materials with different polarizations  $p$ , then  $\text{curl}(\mathbf{j}/D) \neq 0$  and thus  $\mathbf{j} \neq 0$ . Of course, the current cannot cross an outer boundary of an electrically disconnected device, and thus circulates inside, forming closed loops.

These loops cannot be confined to any of the uniform parts of the device, but necessarily cross the boundaries between them. Indeed, the presence of a current loop in a region of constant  $D$  and  $p$  would mean  $\text{curl}\mathbf{j} \neq 0$ , which is impossible due to Eq. (2): in uniform regions,  $\mathbf{j}$  is the gradient of a function. Thus, the current lines

must form a vortex with the core somewhere at the F/N boundary.

The Eq. (2) can also be interpreted as follows. Electric current is driven by two forces: one is the conventional electrochemical potential gradient, and the other is an effective electromotive force (EMF)  $\mathcal{E} = -(pD/2)\nabla\mu^s$  due to the non-equilibrium spin accumulation  $\mu^s$ . Both the  $\mu^s$  and its gradient decay away from the spin current injection point, thus an EMF region appears around it (Fig. 2(a)), producing the current loops.

Generation of electric current vortices is not limited to spintronics. Consider coupled electric and heat transport

$$\begin{aligned} \mathbf{j} &= -\sigma\nabla\mu - S\sigma\nabla T, \\ \mathbf{q} &= -\Pi\sigma\nabla\mu - \kappa\nabla T, \end{aligned} \quad (6)$$

where  $\mathbf{q}$  is the heat flux,  $\kappa$  is the thermal conductivity, and  $S$  and  $\Pi$  are Seebeck and Peltier coefficients. Similarly to how the Eq. (5) follows from the Eq. (2), the Eq. (6) implies that a temperature gradient satisfying  $\nabla S \times \nabla T \neq 0$  produces current loops at the interface between materials with different Seebeck coefficients.

Now, we choose a symmetric device in Fig. 2(b) as a simple setting to solve the Valet-Fert equations and demonstrate the loop current generation in a specific geometry. As the thickness  $t_N$  of the normal metal film decreases, we expect the spin accumulation to become ever more uniform across the N-film. Then the solution for a realistic device with pure spin current injected from the side as in Fig. 2(a) will be the same as for injection from below, as in Fig. 2(b). In the latter case, electric current bursts into the ferromagnet like water from a fountain, and flows back through the normal film: we will call it a “spin fountain” device.

We place the origin at the spin injection point, and direct the  $\hat{x}$  axis along the F/N boundary, the  $\hat{y}$  axis transversely to it, and the  $\hat{z}$  axis normal to the plane of Fig. 2. We assume all the quantities to be  $z$ -independent, thus reducing the problem to two dimensions. For brevity, we introduce notations  $\lambda_n \equiv \lambda_s(N)$ ,  $\lambda_f \equiv \lambda_s(F)$ ,  $D_N \equiv D(N)$ ,  $D_F \equiv D(F)$ , and  $p \equiv p(F)$ . For the reasons explained above, we assume  $t_N/\lambda_n \ll 1$ , while  $t_F/\lambda_f$  can take any value.

In the ferromagnet, potentials  $(\mu, \mu^s)$  are governed by Eqs. (4). We switch to a “mixed potential”  $M = \mu + p\mu^s/2$ . In terms of  $(M, \mu^s)$ , the bulk equations decouple:

$$\Delta M = 0, \quad \lambda_f^2\Delta\mu^s = \mu^s. \quad (7)$$

The price to pay for this simplification is the change of the boundary conditions. While  $\mu^s$  remains continuous,  $M$  experiences a jump  $M_F - M_N = (p/2)\mu^s$  at the F/N interface. Expressions for the currents now read

$$\mathbf{j} = -D\vec{\nabla}M, \quad (8)$$

$$\mathbf{j}^s = -\frac{D}{2}\left((1-p^2)\vec{\nabla}\mu^s + 2p\vec{\nabla}M\right) \quad (9)$$

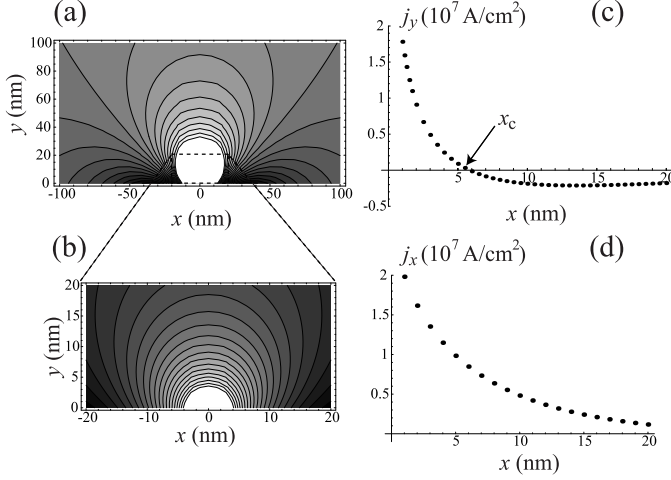


FIG. 3: (a) Contour plot of the mixed potential  $M_F(x, y)$  for  $t_F \rightarrow \infty$ . Electric current  $\mathbf{j}$  is perpendicular to the contours, Eq. (8). (b) Blow-up of (a) near the origin. (c) Normal component  $j_y$  of electric current at the F/N boundary. The zero of  $j_y$  defines the position  $x_c$  of the vortex core. (d) Component  $j_x$  along the F/N boundary, in the F-layer.

In the normal film, we approximate  $\mu_N(x, y) \approx \mu_N(x)$ ,  $\mu_N^s(x, y) \approx \mu_N^s(x)$  and derive the effective equations for potentials averaged over the film thickness:

$$\begin{aligned} R \partial_x^2 M_N &= -\frac{1}{t_N} \partial_y M_F(x, 0) \\ \lambda_n^2 \partial_x^2 \mu_N^s &= \mu_N^s - \frac{\lambda_{mix}^2}{t_N} \times \\ &\times \partial_y \left[ \mu_F^s(x, 0) + \frac{2p}{1-p^2} M_F(x, 0) \right] - s \delta(x) \end{aligned} \quad (10)$$

where  $R = D_N/D_F$ ,  $\lambda_{mix}^2(p) = (1-p^2)\lambda_n^2/R$ , and  $s$  is a rescaled total injected spin current.

In the ferromagnet, we seek the potentials in the form

$$\begin{aligned} \mu_F^s(x, y) &= \int \frac{dk}{2\pi} a_k \cos(kx) \frac{\cosh[q(k)(t_F - y)]}{\cosh[q(k)t_F]}, \\ M_F(x, y) &= \int \frac{dk}{2\pi} b_k \cos(kx) \frac{\cosh[k(t_F - y)]}{\cosh[kt_F]}. \end{aligned} \quad (11)$$

With  $q^2(k) = \lambda_f^{-2} + k^2$ , the  $\mu_F^s$  and  $M_F$  automatically satisfy the Eqs. (7) and the boundary conditions  $j_\perp = 0$ ,  $j_\perp^s = 0$  at the top surface  $y = t_F$  of the ferromagnet.

In the normal film  $\mu_N^s(x) = \mu_F^s(x, 0)$ , and  $M_N$  is found from the boundary condition on its jump:

$$M_N(x) = \int \frac{dk}{2\pi} \left( b_k - \frac{p}{2} a_k \right) \cos(kx). \quad (12)$$

Substituting the Fourier expansions into the Eqs. (10), we find the coefficients

$$a_k = \frac{s}{F(k)}, \quad b_k = \frac{p}{2} \frac{sH(k)}{F(k)}. \quad (13)$$

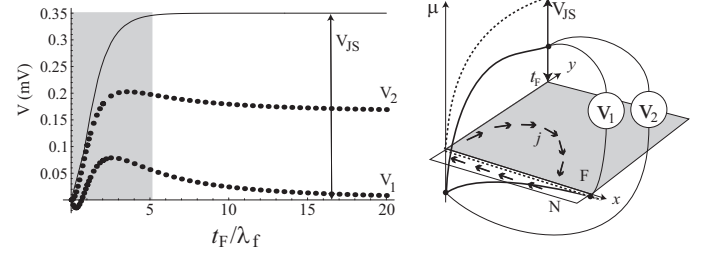


FIG. 4: (a) Voltages  $V_{1,2}(t_F)$  measured in a spin-fountain device by voltmeters shown in (b). Solid line shows the voltage measured by either of the two voltmeters in a device with uniform spin injection. Gray area marks the region where  $\mu_s$  does not fully relax at  $y = t_F$ . (b) Sketch of electric potential  $\mu(x, y)$  in the device. Arrows in the  $(x, y)$  plane show the flow of electric current. Solid lines: actual  $\mu(x, 0)$  and  $\mu(0, y)$ . Dotted lines: the same for uniform injection.

with

$$\begin{aligned} F(k) &= f(k) + \frac{p^2}{1-p^2} \frac{\lambda_{mix}^2}{t_N} H(k) k \tanh(t_F k) \\ f(k) &= 1 + \lambda_n^2 k^2 + \frac{\lambda_{mix}^2}{t_N} q(k) \tanh(t_F q(k)) \\ H(k) &= \frac{R t_N k}{R t_N k + \tanh(t_F k)} \end{aligned} \quad (14)$$

As per Eq. (13), at  $p = 0$  the electric current vanishes.

Solutions (11) are computed by numerical integration. The magnitude of electric current is proportional to the injected spin current  $s$ . To compare with experiment, we rescale  $s$  so that spin accumulation  $\mu_0^s$  at the injection point has the largest feasible value, estimated [8, 9] as  $\mu_0^s \sim 1$  mV. Electric current can be found from (8) using the parameters, typical of a Py/Cu device in the Ref. [6]:  $\lambda_n = 350$  nm,  $\lambda_f = 4.3$  nm,  $t_N = 2$  nm,  $p = 0.7$ ,  $R = 6.6$ , and  $\sigma(Cu) = 48 \cdot 10^6$  ( $\Omega \cdot m$ )<sup>-1</sup>.

A contour plot of  $M(x, y)$  for  $t_F \rightarrow \infty$  is shown in Fig. 3(a,b). Electric current is normal to  $M = \text{const}$  lines (8) and forms a fountain-like pattern sketched in Fig. 2(b). Figs. 3(c,d) give the current components at the F/N interface. Note that in our model both  $j_x$  and  $j_y$  diverge at the origin because a point source of spin current was assumed. At  $x \ll \lambda_\parallel$ , we find  $j \propto \ln(\lambda_\parallel/x)$ . In a real experiment, the current density profile will be determined by the size of the pure spin injector.

Induced electric current significantly alters the voltage measured in a Johnson-Silsbee experiment and makes it dependent on the position of the voltmeter probe. Let us assume that the F-probe is attached at the top of the F-layer, right above the injection point. For an extended F-electrode, the easiest way to attach an N-probe is at  $x_N \rightarrow \infty$  (Fig. 4, b). Then the measured voltage  $V_1(t_F) = \mu(0, t_F) - \mu(x_N, 0) \rightarrow \mu(0, t_F)$ . The plot of  $V_1(t_F)$  is given in Fig. 4(a). If the N-probe is attached close to the spin-injection point, the voltage changes to

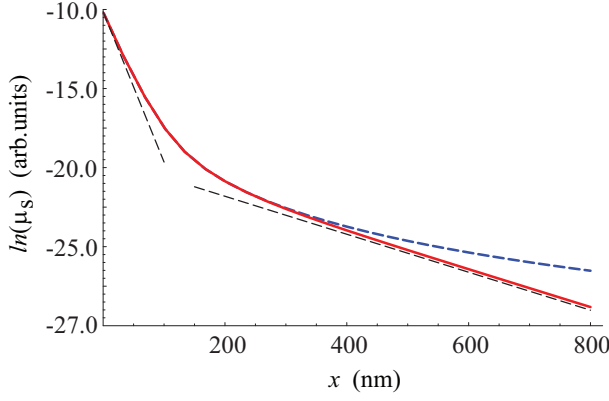


FIG. 5: (Color online) Log plot of spin potential. Red, solid line:  $\mu^s(x, 0)$  for  $t_F = 250$  nm. Blue, dashed line:  $\mu^s(x, 0)$  for  $t_F \rightarrow \infty$ . Dashed linear fits: short-range exponential decay with  $\lambda_{||} = 10.5$  nm and long-range exponential decay with  $\lambda_c \approx 83$  nm.

$V_2$ . Both  $V_1$  and  $V_2$  significantly differ from the voltage that would develop in the absence of electric current (solid line in Fig. 4-a). Dependence on the F-electrode thickness is also quite visible even for  $t_F \gg \lambda_f$ . The  $j = 0$  situation emerges either in a narrow F-electrode, or, more generally, in devices where spin is injected uniformly across the F/N interface: The Eq. (5) shows that, when  $\nabla\mu^s$  is normal to the boundary, the reason for current generation vanishes together with  $\text{curl}\mathbf{j}$ . Uniform spin injection generates voltage that approaches the Johnson and Silsbee result  $V_{JS} = (p/2)\mu_0^s = 0.35$  mV for  $y \gg \lambda_f$ .

Note that the results shown in the Fig. 4(a) are valid independently of the voltmeter probe material only if spin accumulation at  $y = t_F$  has relaxed to zero, that is for  $t_F \gg \lambda_f$ . Inside the gray area in Fig. 4(a), the actual material-dependent boundary condition should be applied at  $y = t_F$  instead of the zero spin current condition we used.

Due to spin relaxation in the bulk, spin currents tend to decay exponentially with the distance from the injection point. When the top layer is non-magnetic ( $p = 0$ ), in the present case of  $Rt_N \gg \lambda_f$  we find  $a_k \approx 1/(f(0) + \lambda_n^2 k^2)$ . In this limit, the spin potential falls off as  $\mu^s(0, y) \approx \mu_0^s \exp(-y/\lambda_f)$  transversely to the F/N interface, and as  $\mu^s(x, 0) \approx \mu_0^s \exp(-x/\lambda_{||})$  along the interface. The decay length  $\lambda_{||} = \lambda_n/\sqrt{f(0)}$  is bound as per  $\lambda_f < \lambda_{||} < \lambda_n$ . Physically, this means that spins would propagate through a detached normal metal film up to a length of about  $\lambda_n$ , but the spin current leakage into the overlayer shortens their reach.

For a magnetic top layer ( $p \neq 0$ ), a log plot of  $\mu^s(x, 0)$  is shown in Fig. 5: the  $\mu^s(x, 0)$  decays exponentially. However, the decay length crosses over from  $\lambda_{||}$  at  $x \ll t_F$  to a longer length  $\lambda_c$  at  $x \gg t_F$ . In the crossover region,

the decay is non-exponential. The value of  $\lambda_c$  can be found from the poles of  $a_k$  in the complex plane: they are located on the imaginary axis  $k = i\kappa$ . The pole  $k = i\kappa_c$  nearest the origin gives the long-range decay length  $\lambda_c = 1/\kappa_c$ . In the thick-film limit  $t_F \gg Rt_N$ , we find

$$\lambda_c \approx \frac{t_F}{\pi} \left( 1 + \frac{Rt_N}{t_F} + \dots \right).$$

For the parameters above, this yields  $\lambda_c \approx 84$  nm against the numerically found  $\lambda_c \approx 83$  nm.

The  $\lambda_c$  grows with  $t_F$  and, at  $t_F \rightarrow \infty$ , the  $\mu^s(x, 0)$  decays non-exponentially for  $x \gg \lambda_{||}$ . In this limit,  $\tanh(t_F k) \rightarrow \text{sgn}(k)$  is non-analytic at  $k = 0$ , and the expressions for  $F(k)$  and  $H(k)$  read

$$F(k) = f(k) + \frac{p^2}{1-p^2} \frac{\lambda_{mix}^2}{t_N} H(k)|k|, \quad H(k) = \frac{Rt_N|k|}{Rt_N|k| + 1}. \quad (15)$$

The singularity shows itself as a  $|k|^3$  term in the expansion of  $a_k$ . Using the stationary phase method we find an asymptotic expression

$$\mu^s(x, 0) \sim \frac{C}{x^4} + \dots \quad (|x| \gg \lambda_{||}) \quad (16)$$

with  $C = s(p^2/(1-p^2))(6R^2/\pi f^2(0))\lambda_{mix}^2 t_N$ . Thus, in the  $t_F \rightarrow \infty$  limit, at  $x \gg \lambda_{||}$  spin accumulation decays as power-law, i.e. very slowly (blue line in Fig. 5).

To summarize, we find that a ferromagnetic overlayer makes the injected spin current propagate further along the normal film. This conclusion sounds pronouncedly counter-intuitive: After all, ferromagnetic layer is known to be a spin sink, so one would expect that it could only lower the spin propagation length. The seeming paradox is resolved as follows. As we know, the electric current vortices cross the F/N boundary. Upon such crossing, a non-equilibrium spin density is inevitably produced [3], so  $\mu^s$  cannot decay independently of  $\mathbf{j}$ . Ultimately the conservation of  $\mathbf{j}$ , reflected in the first equation of (1), causes a long-range propagation of both current and spin. The current-assisted propagation of spin also explains the role of the F-layer thickness. The long-range pattern of  $\mathbf{j}$  is limited by the outer boundaries of the device. Finite  $t_F$  is equivalent to “covering the fountain by a lid”, deflecting  $\mathbf{j}$  down to the normal film within a distance of the order of  $t_F$ . Beyond this distance, the power-law decay of spin accumulation reverts to the exponential form.

In conclusion, we have shown that gradient of spin accumulation along an F/N interface produces closed electric current loops, that may significantly modify the Johnson-Silsbee voltage measured between the F and N parts of the device. These electric currents lead to long-range propagation of spin accumulation along the F/N interface. We have also shown that, more generally, electric current vortices at the interface between two materials shall be expected whenever electric current is coupled

to another driven diffusive current by linear relationships with Onsager cross-coefficients, that are different for the two materials.

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